

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	8.5mΩ@10V	15A
	10.0mΩ@4.5V	



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

技术 品质 服务

www.siliup.com

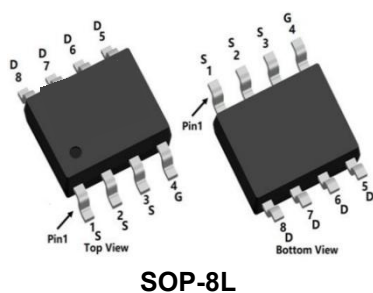
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

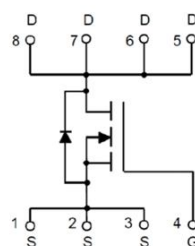
Applications

- Power switching application
- Battery management
- Uninterruptible power supply

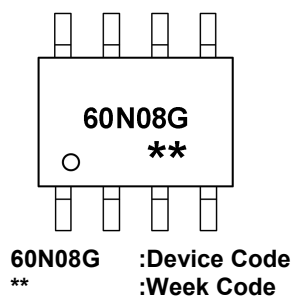
Package



Circuit Diagram



Marking



Order Information

Device	Package	Unit/Tape
SP60N08GP8	SOP-8L	4000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Ta=25°C)	I_D	15	A
Continuous Drain Current (Ta=100°C)	I_D	10	A
Pulse Drain Current Tested	I_{DM}	60	A
Single Pulse Avalanche Energy ¹	E_{AS}	91	mJ
Power Dissipation (Ta=25°C)	P_D	3.1	W
Power Dissipation (Ta=100°C)	P_D	1.24	W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	40.3	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

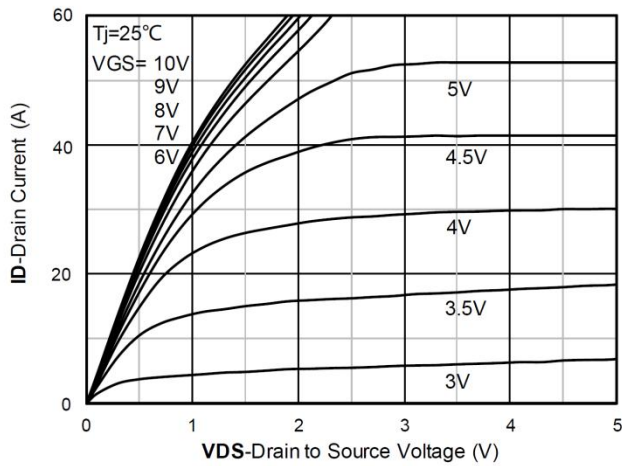
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V, ID=250uA	60	-	-	V
Drain Cut-Off Current	I _{DSS}	VDS=48V, VGS=0V	-	-	1	uA
Gate Leakage Current	I _{GSS}	VGS=±20V, VDS=0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	VDS=VGS, ID=250uA	1.1	1.5	2.1	V
Drain-Source ON Resistance	R _{DS(ON)}	VGS=10V, ID=10A	-	8.5	11.5	mΩ
		VGS=4.5V, ID=8A	-	10	14.5	
Gate Resistance	R _G	VDS=30V , VGS=0V , f=1MHz	-	2.1	-	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	VDS=30V , VGS=0V , f=1.0MHz	-	998	-	pF
Output Capacitance	C _{oss}		-	242	-	
Reverse Transfer Capacitance	C _{rss}		-	11	-	
Total Gate Charge	Q _g	VDS=30V , VGS=10V , ID=20A	-	14	-	nC
Gate-Source Charge	Q _{gs}		-	3	-	
Gate-Drain Charge	Q _{gd}		-	3.5	-	
Gate Plateau Voltage	V _{plateau}		-	3.7	-	V
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	VGS=10V , VDS=30V , ID=20A , RG=4.7Ω	-	7	-	nS
Rise Time	t _r		-	4	-	
Turn-Off Delay Time	t _{d(off)}		-	23	-	
Fall Time	t _f		-	4	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	15	A
Reverse Recovery Time	T _{rr}	IS=30A , di/dt=100A/us , TJ=25℃	-	36	-	nS
Reverse Recovery Charge	Q _{rr}		-	23	-	nC

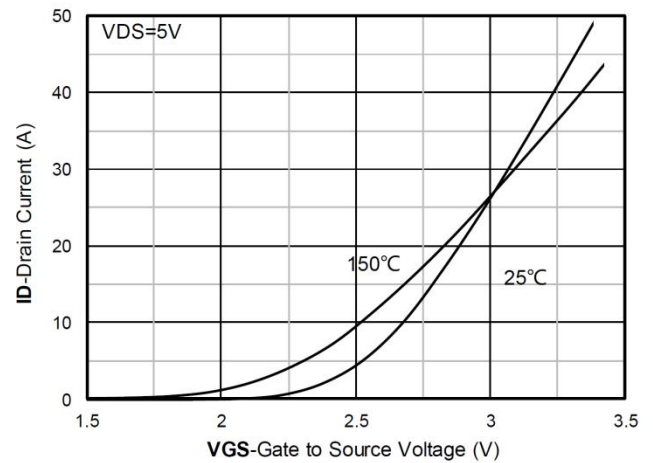
Note:

- The EAS test condition is $V_{DD}=30V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$;

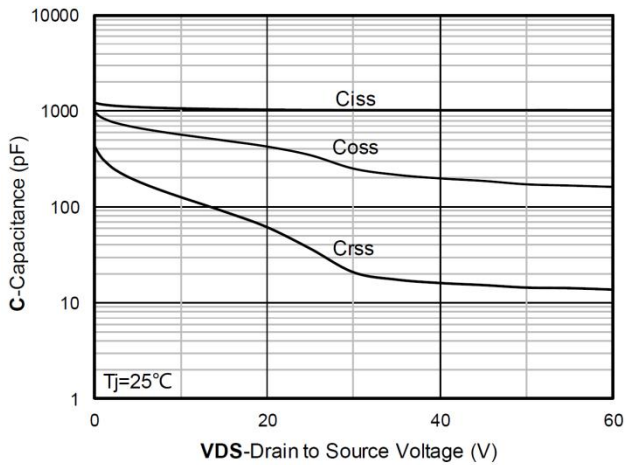
Typical Characteristics



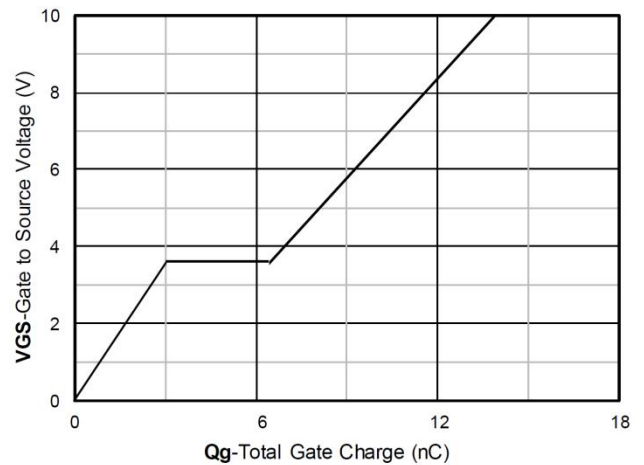
Output Characteristics



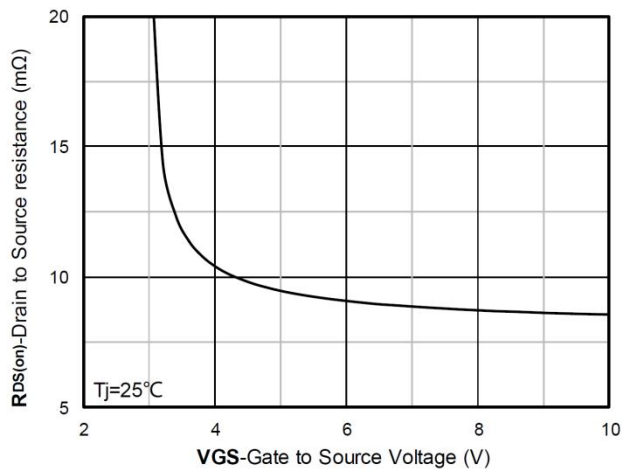
Transfer Characteristics



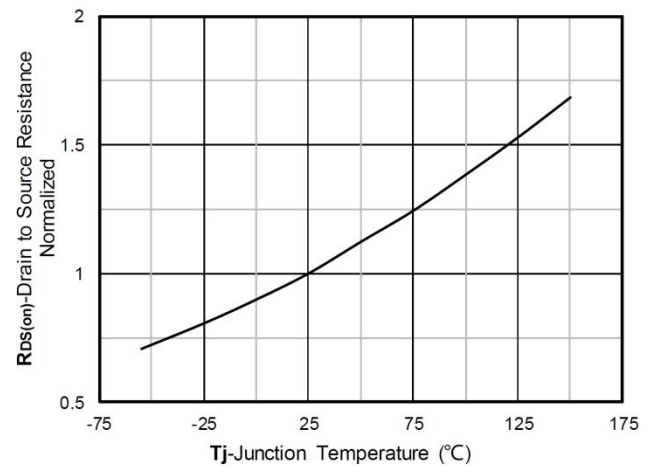
Capacitance Characteristics



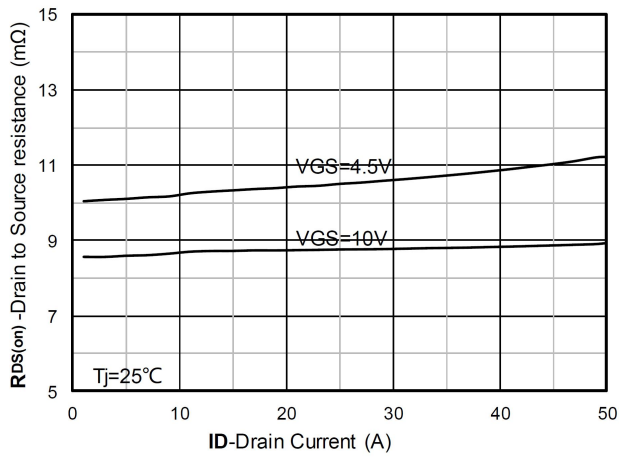
Gate Charge



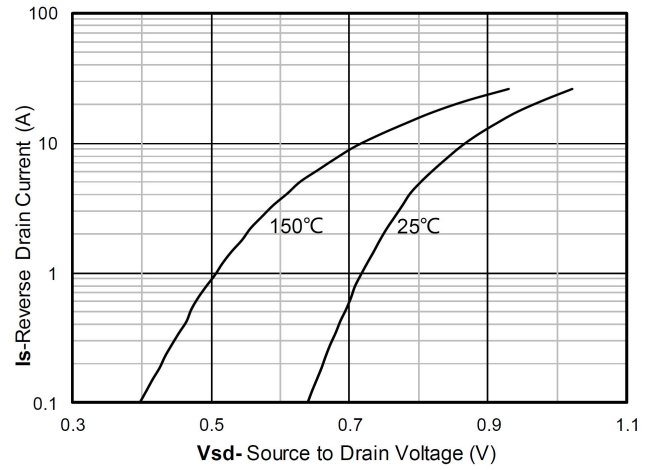
On-Resistance vs Gate to Source Voltage



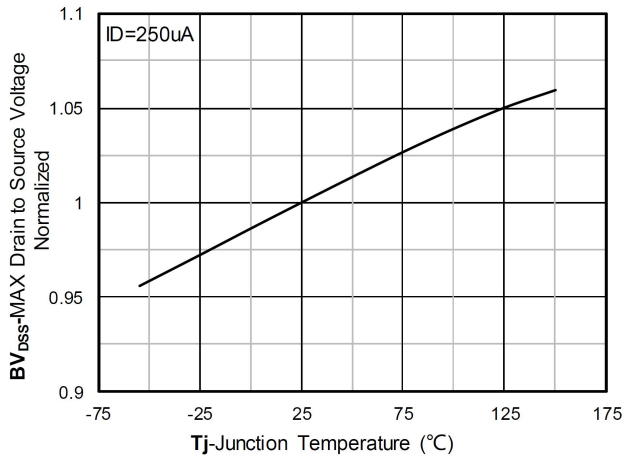
Normalized On-Resistance



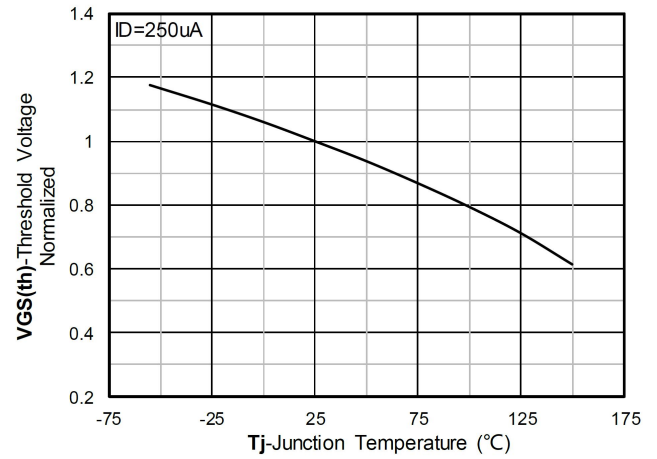
RDS(on) VS Drain Current



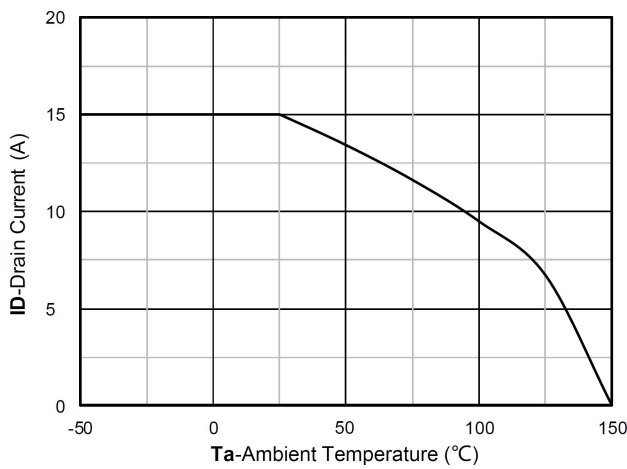
Forward characteristics of reverse diode



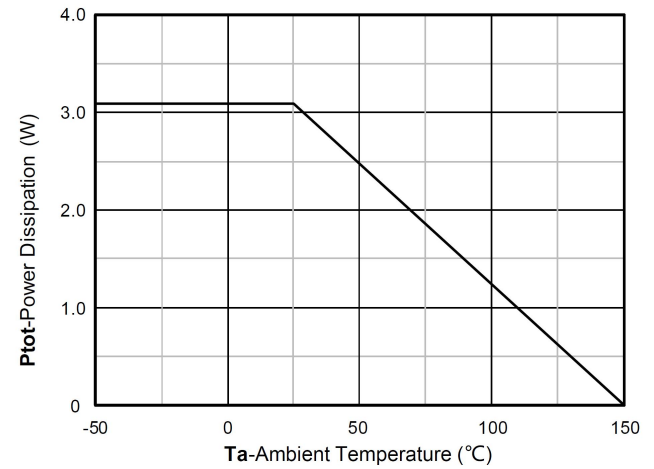
Normalized breakdown voltage



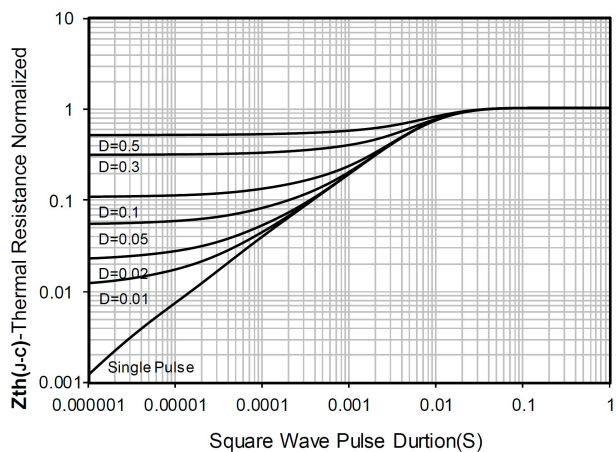
Normalized Threshold voltage



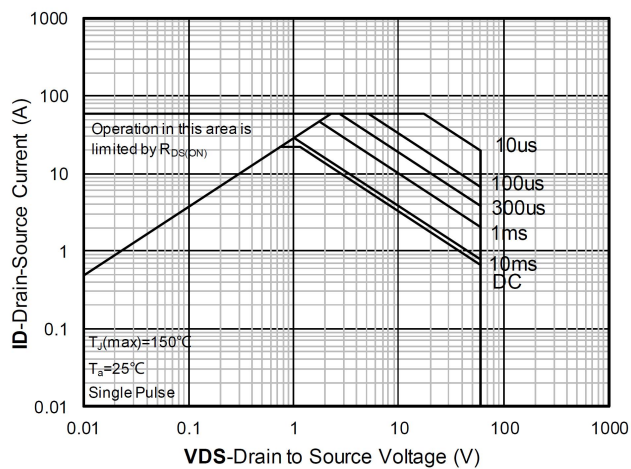
Current dissipation



Power dissipation



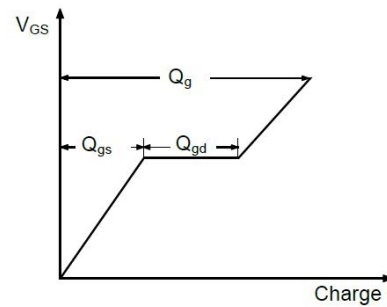
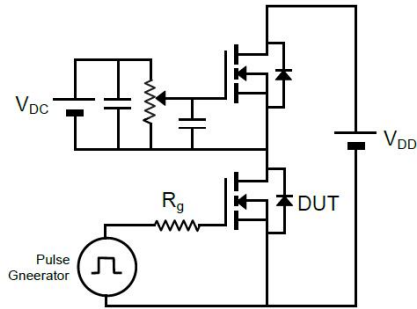
Normalized Maximum Transient Thermal Impedance



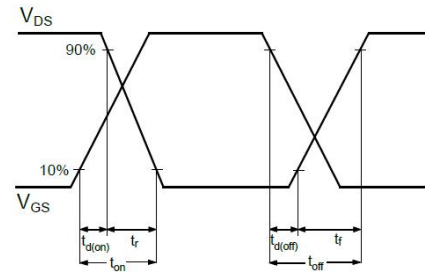
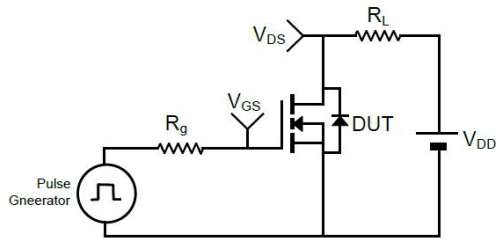
Safe Operation Area

Test Circuit

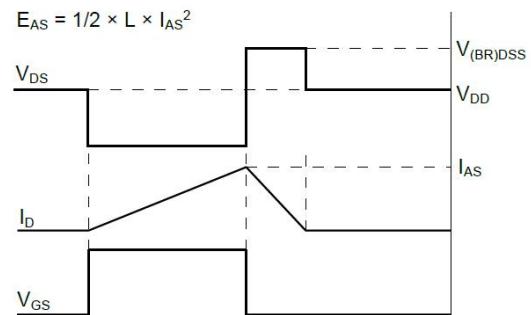
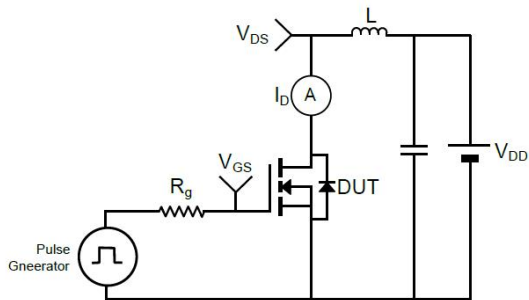
Gate Charge



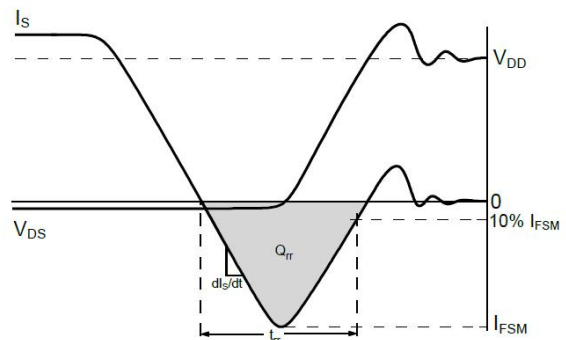
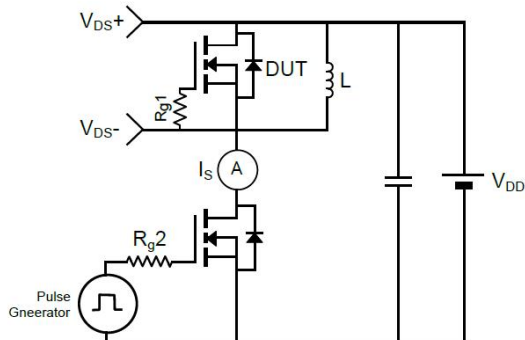
Resistive Load Switching Time

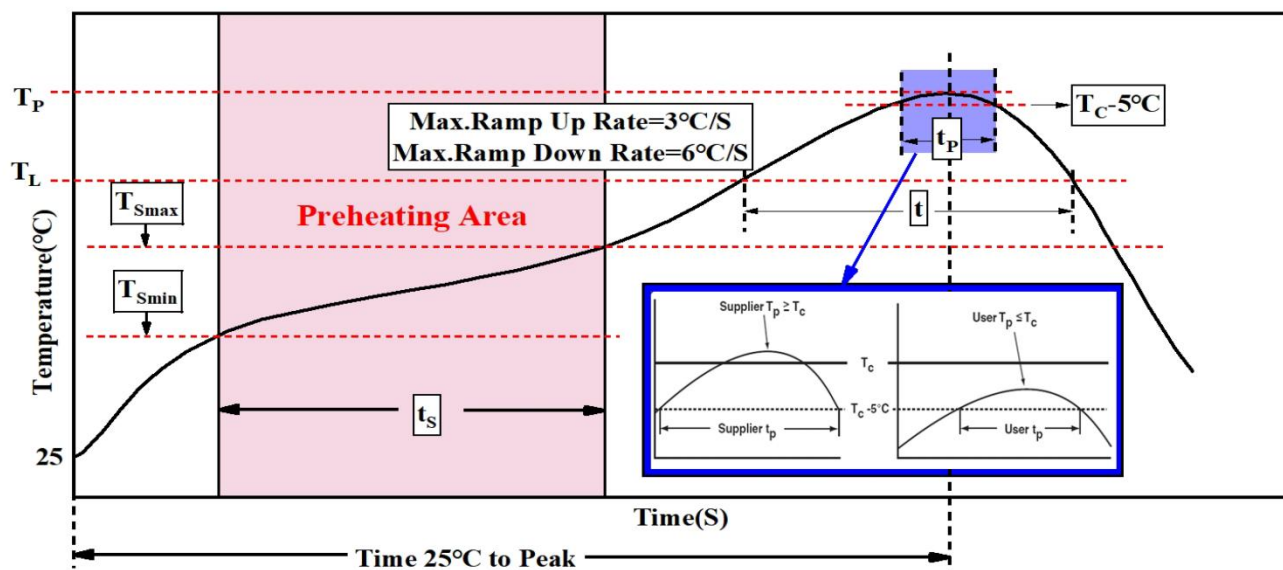


Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering


Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{Smin})	100°C	150°C
Temperature max (T_{Smax})	150°C	200°C
Time (T_{Smin} to T_{Smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{Smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217°C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_C)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{Smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_P) is defined as a supplier minimum and a user maximum		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_C)

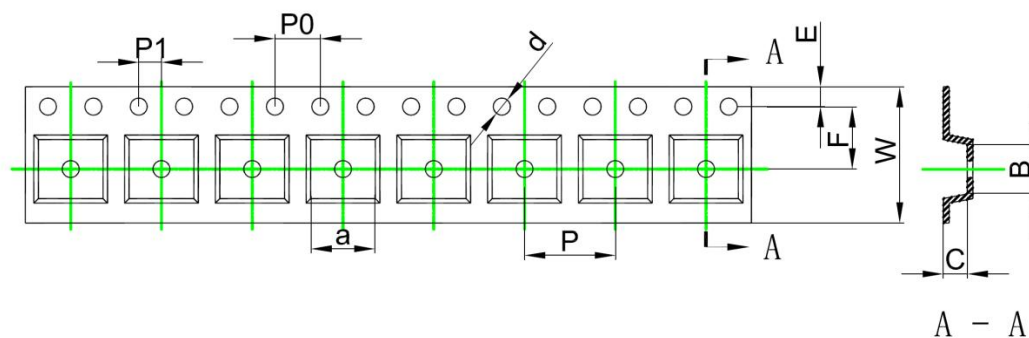
Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C



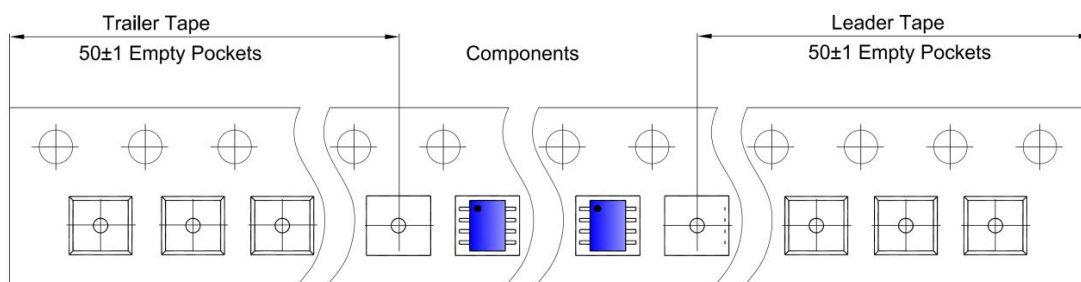
SOP8 Embossed Carrier Tape



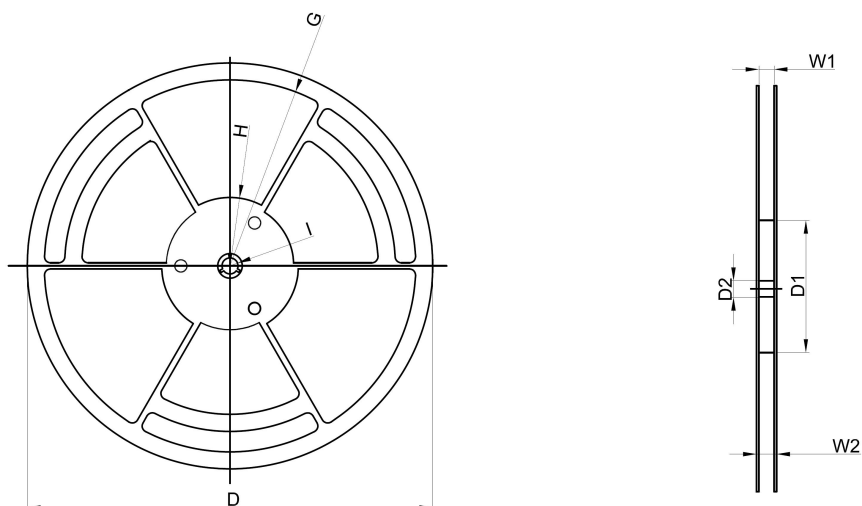
Dimensions are in millimeter

Pkg type	a	B	c	d	E	F	P0	P	P1	W
SOP-8	6.40	5.40	2.10	$\Phi 1.50$	1.75	5.50	4.00	8.00	2.00	12.00

SOP8 Tape Leader and Trailer



SOP8 Reel

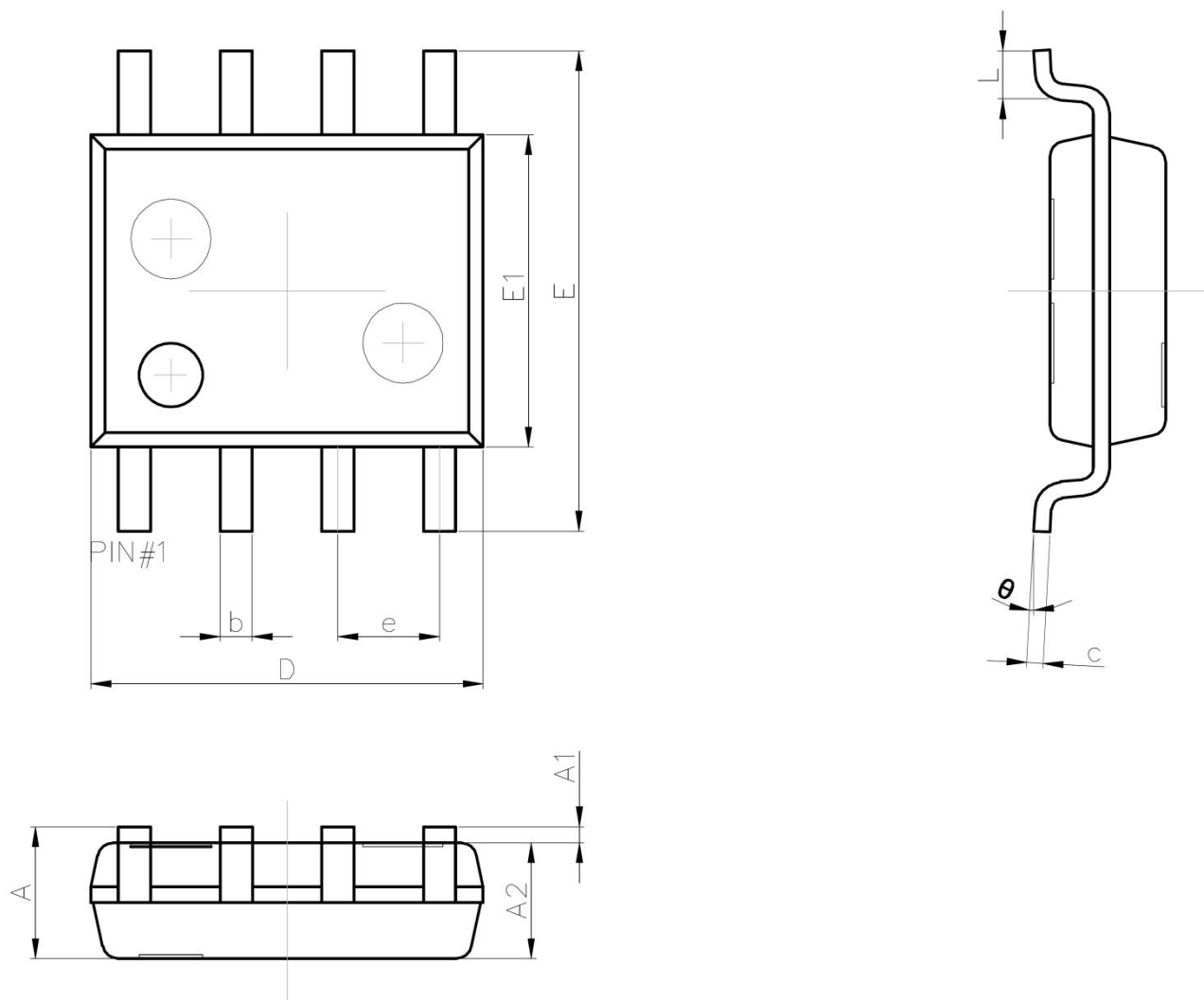


Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
13" Dia	Ø330.00	100.00	13.00	R151.00	R56.00	R6.50	12.40	17.60

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
4,000 pcs	13 inch	8,000 pcs	360×360×65	40,000 pcs	565×380×390	

SOP-8L Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°